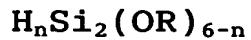


## ABSTRACT

[Abstract]

[Problems] It is to provide a method for producing a silicon oxide film having better quality than a TEOS at low temperature. And it is to provide a method for manufacturing a semiconductor device wherein an insulating film composed of a silicon oxide is formed.

[Means for solving problems] A film composed of a silicon oxide is produced by CVD method where a silane compound represented by the following general formula is reacted. An insulating film is deposited by CVD method where a silane compound represented by the following general formula is reacted.



(In the above formula, R is an alkyl group of carbon number from 1 to 5, and n is an integer from 0 to 2.)